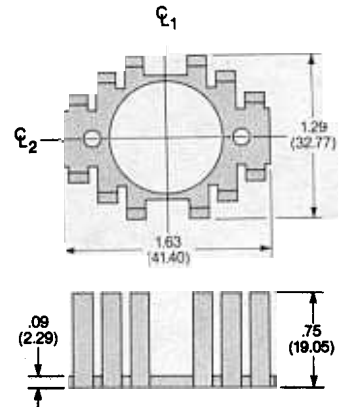
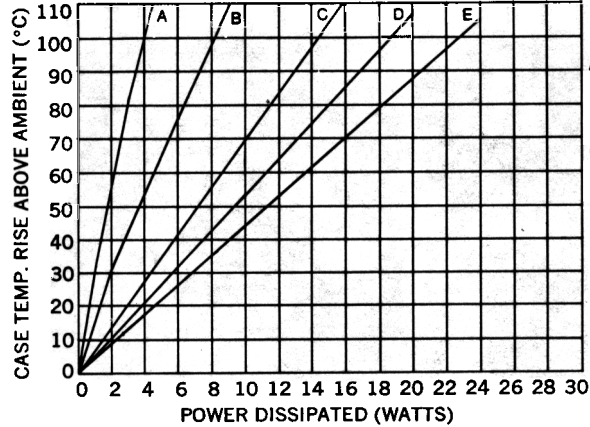


LA363B3



Dimensions are for reference use only. Contact IERC for dimensions with tolerances or standard part drawings.

LA363B3CB w/2N3055 (TO-3) TRANSISTOR



DESCRIPTION OF CURVES
 A. N.C. Horiz. Device Only Mounted to G-10.
 B. N.C. Horiz. & Vert. With Dissipator.
 C. 200 FPM w/Diss.
 D. 500 FPM w/Diss.
 E. 1000 FPM w/Diss.

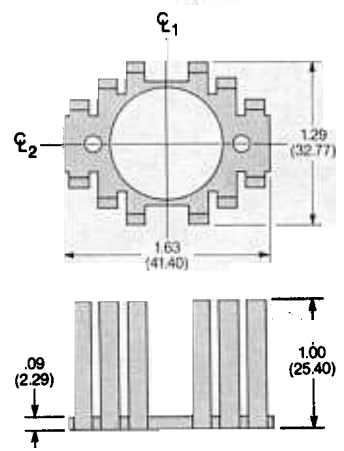
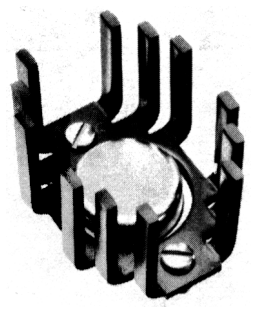
- Thermal Resistance Case to Sink is 1.0-1.4 °C/W w/Joint Compound.
- Derate 0.7 °C/watt for unplated part in natural convection only.
- Derate 3.0 °C/watt for Insulube® part in natural convection only.

Ordering Information

IERC PART NO.				Semiconductor Accommodated	Hole patt. ref. no. (see pg. 1-26)	Max. Weight (Grams)
Unplated	Comm'l. Black Anodize	Mil. Black Anodize	Insulube® 448			
LA363B3U	LA363B3CB	LA363B3B	LA363B3	Any TO-3 can	3	8.2

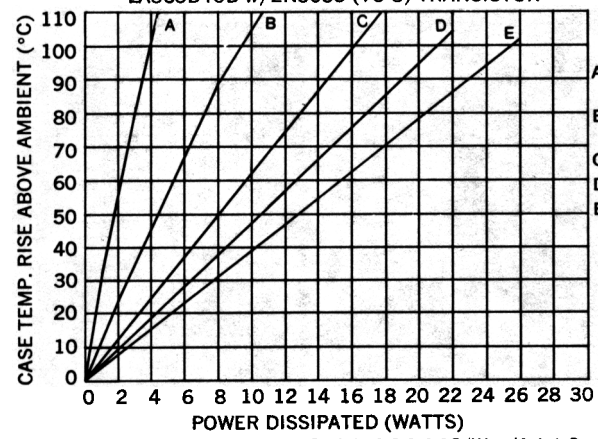
Note: See page iv for other finishes.

LA363B4



Dimensions are for reference use only. Contact IERC for dimensions with tolerances or standard part drawings.

LA363B4CB w/2N3055 (TO-3) TRANSISTOR



DESCRIPTION OF CURVES
 A. N.C. Horiz. Device Only Mounted to G-10.
 B. N.C. Horiz. & Vert. With Dissipator.
 C. 200 FPM w/Diss.
 D. 500 FPM w/Diss.
 E. 1000 FPM w/Diss.

- Thermal Resistance Case to Sink is 1.0-1.4 °C/W w/Joint Compound.
- Derate 0.7 °C/watt for unplated part in natural convection only.
- Derate 3.0 °C/watt for Insulube® part in natural convection only.

Ordering Information

IERC PART NO.				Semiconductor Accommodated	Hole patt. ref. no. (see pg. 1-26)	Max. Weight (Grams)
Unplated	Comm'l. Black Anodize	Mil. Black Anodize	Insulube® 448			
LA363B4U	LA363B4CB	LA363B4B	LA363B4	Any TO-3 can	3	10.4

Note: See page iv for other finishes.